

☒ Drafts
☒ IS&R:
☒ Pending
☒ Active
 L1: (2257620) current
 L2: (4328796) increase or increases or
 L3: (134855) erasing or erase or erase
 L4: (907652) negative
 L5: (994352) pulse or pulses
 L6: (56746) word adj (line or lines)
 L7: (7904) wordline or wordlines
 L8: (478514) drain
 L9: (2494851) source
 L10: (7170) bitline or bitlines
 L11: (65188) bit adj (line or lines)
 L12: (34164) control adj gate
 L13: (2912) 4 adj5 (6 or 7 or 12)
 L14: (38190) 5 adj5 (8 or 9 or 10 or 1
 L15: (5758) 14 with 1
 L16: (220699) 1 near9 2
 L17: (219) 14 with 16
 L18: (2) 17 same 13 same 3
 L19: (3) 14 same 16 same 13 same 3
 L20: (4584) 4 near9 (6 or 7 or 12)
 L21: (79706) 5 near9 (8 or 9 or 10 or
 L22: (4) 20 same 16 same 21 same 3
 L23: (75) 20 same 21 same 3
 L24: (14) 23 and 16

Default operator: ☒ Highlight all hit terms initially

23 and 16

☒ Failed

	U	1	Document ID	Issue Dat	Pages	Title	Current OR	Curre▲
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20040223	20041111	38	Electrically programmab	365/185.22	365/1
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20040214	20041028	127	Rail stack array of cha	438/149	
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20040206	20041021	126	Dense arrays and charge	257/296	
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20040184	20040923	9	Non-volatile memory era	365/185.18	
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20040012	20040122	10	Non-volatile memory era	365/185.18	
6	<input type="checkbox"/>	<input type="checkbox"/>	US 20030169	20030911	44	Semiconductor memory de	365/185.21	
7	<input type="checkbox"/>	<input type="checkbox"/>	US 20020028	20020307	151	Dense arrays and charge	438/149	257/E
8	<input type="checkbox"/>	<input type="checkbox"/>	US 6807101	20041019	42	Semiconductor memory de	365/185.21	365/1
9	<input type="checkbox"/>	<input type="checkbox"/>	US 6781880	20040824	9	Non-volatile memory era	365/185.18	365/1